HO CHIEN

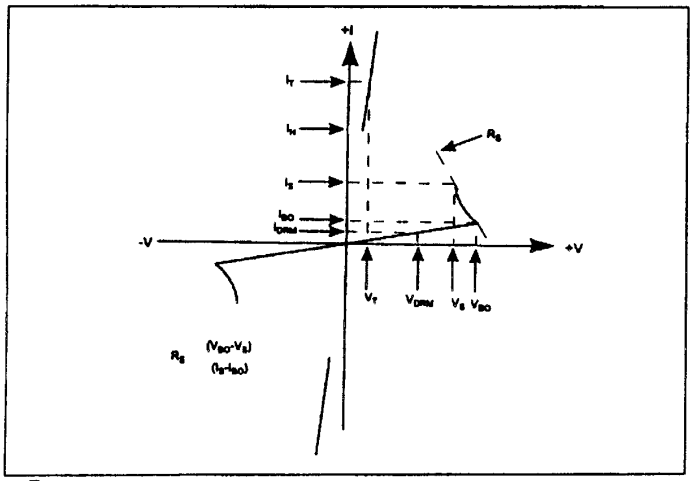
SIDAC

Electrical parameters

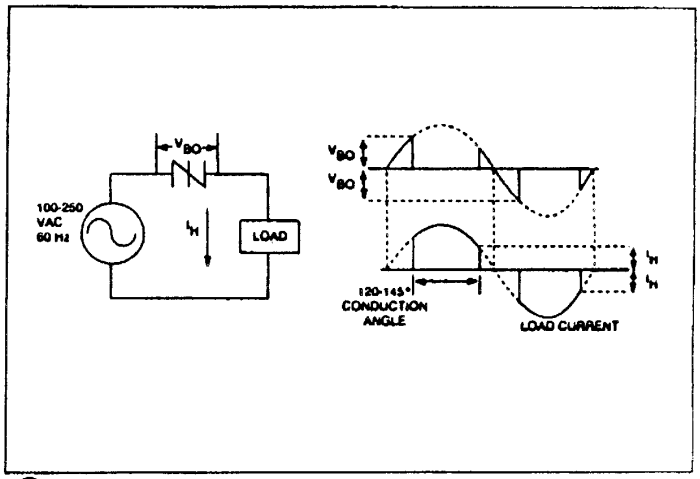
Part Number	V_{BO} Breakover Voltage (Instantancous Clamping voltage) (V) Min.	Max.	I_{BO} Breakover Current (μA) Max.	V_{DRM} Blocking Voltage (V) Min.	I_{DRM} Peak Off-State Current at V_{DRM} (μA) Max.	I_T Continuous On-State DC or RMS Current (A) Max.	I_H Holding Current (mA) Max.	V_{TM} Peak On-State Voltage I_T=1A (V) Max.
K105	95	113	10	75	5	1.0	100	1.5
K110	104	118	10	85	5	1.0	100	1.5
K120	110	125	10	90	5	1.0	100	1.5
K130	120	138	10	95	5	1.0	100	1.5
K140	130	146	10	105	5	1.0	100	1.5
K150	140	170	10	115	5	1.0	100	1.5
K195	165	190	10	130	5	1.0	100	1.5
K200	190	215	10	150	5	1.0	100	1.5
K220	205	230	10	165	5	1.0	100	1.5
K240	220	250	10	175	5	1.0	100	1.5
K250	240	280	10	190	5	1.0	100	1.5
K300	270	330	10	215	5	1.0	100	1.5

Series	**Ipp** Peak Pulse Current Tj<150% (A) (10×160μs) Max	(10×560μs) Max	(10×1000μs) Max	**I_{TSM}** Peak One Cycle(Sinusoidal) Surge Current (A) 60Hz	50Hz	**di/dt** Critical Rate of Rise of On-State Current (A/μs) Typ
K 系列	60	35	35	20	16.7	150

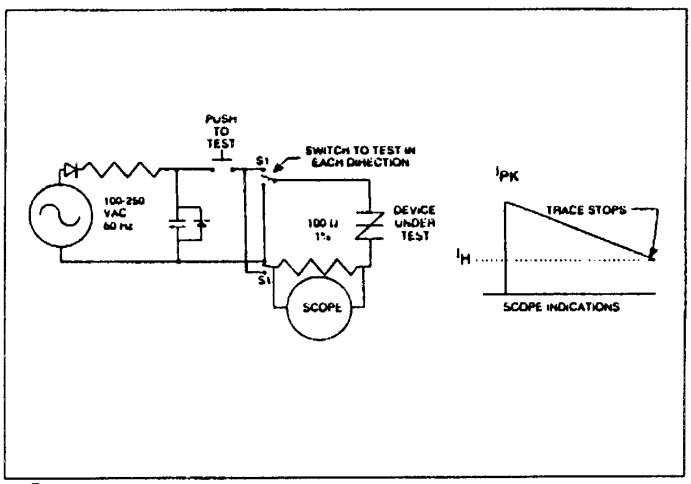
Package : DO15 (K105 ~ K250)
DO201AD (K300)



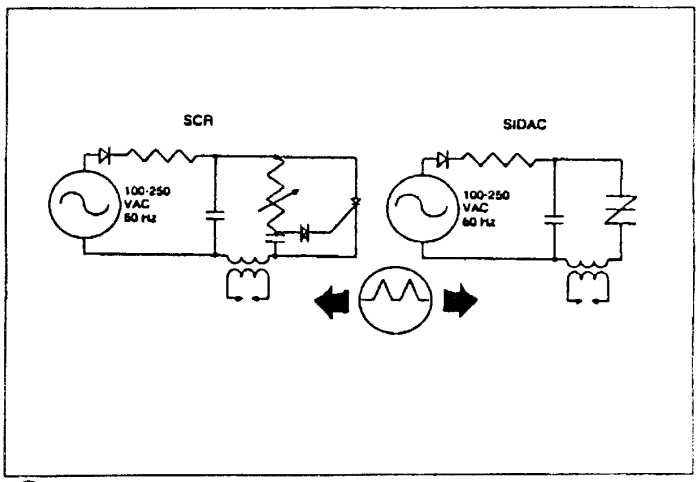
❶ SIDAC V-I 特性



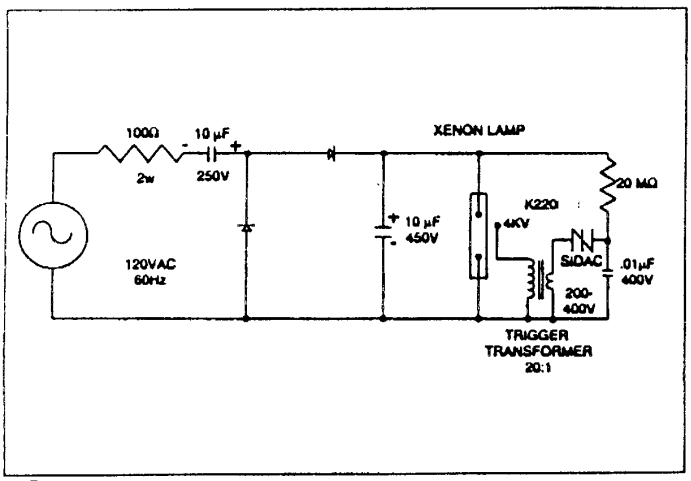
❷ SIDAC 基本电路



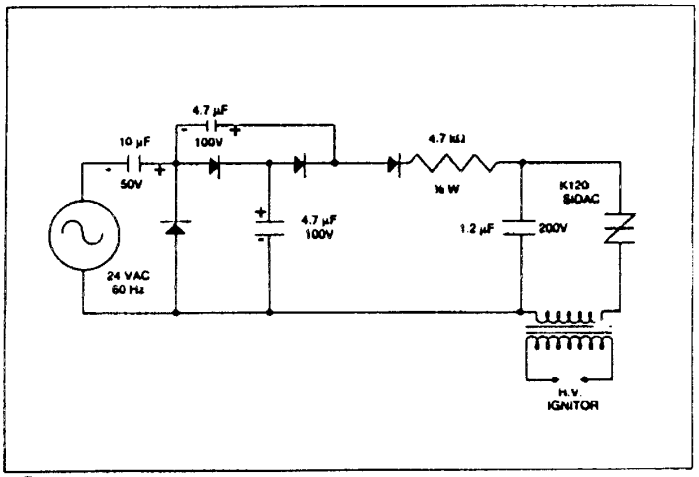
❸ SIDAC 动态保持电流测试电路



❹ SIDAC 与可控硅的比较



❺ 氙灯闪光电路



❻ 点火器电路 (低压输入)

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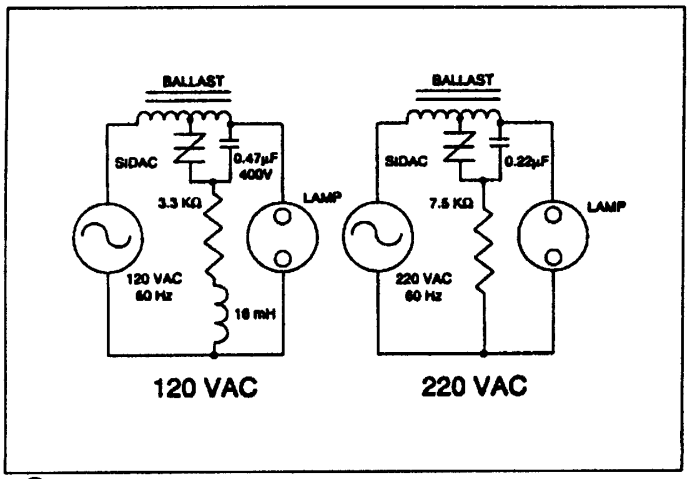
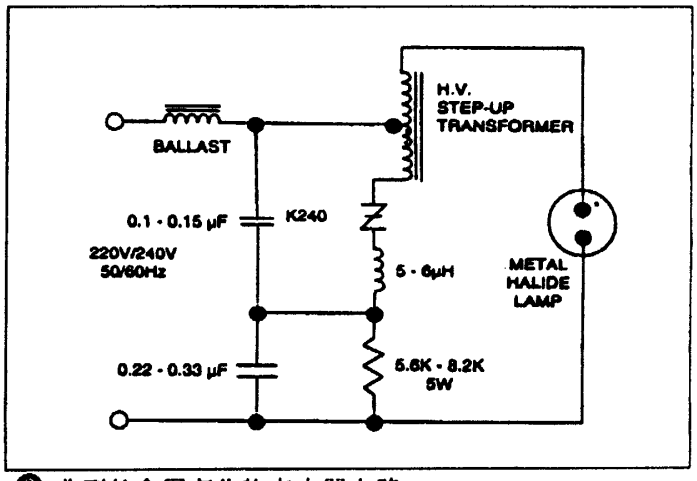
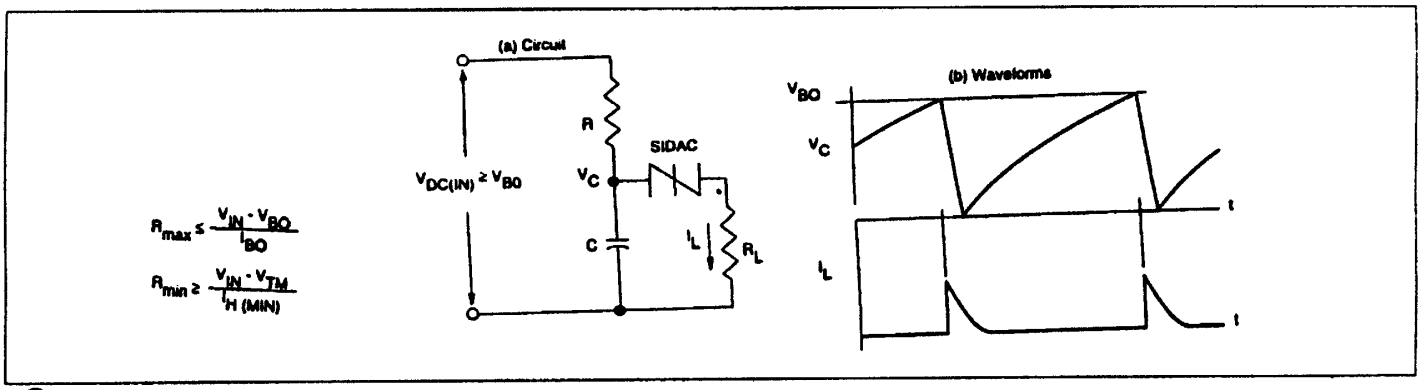
典型应用电路 SIDAC



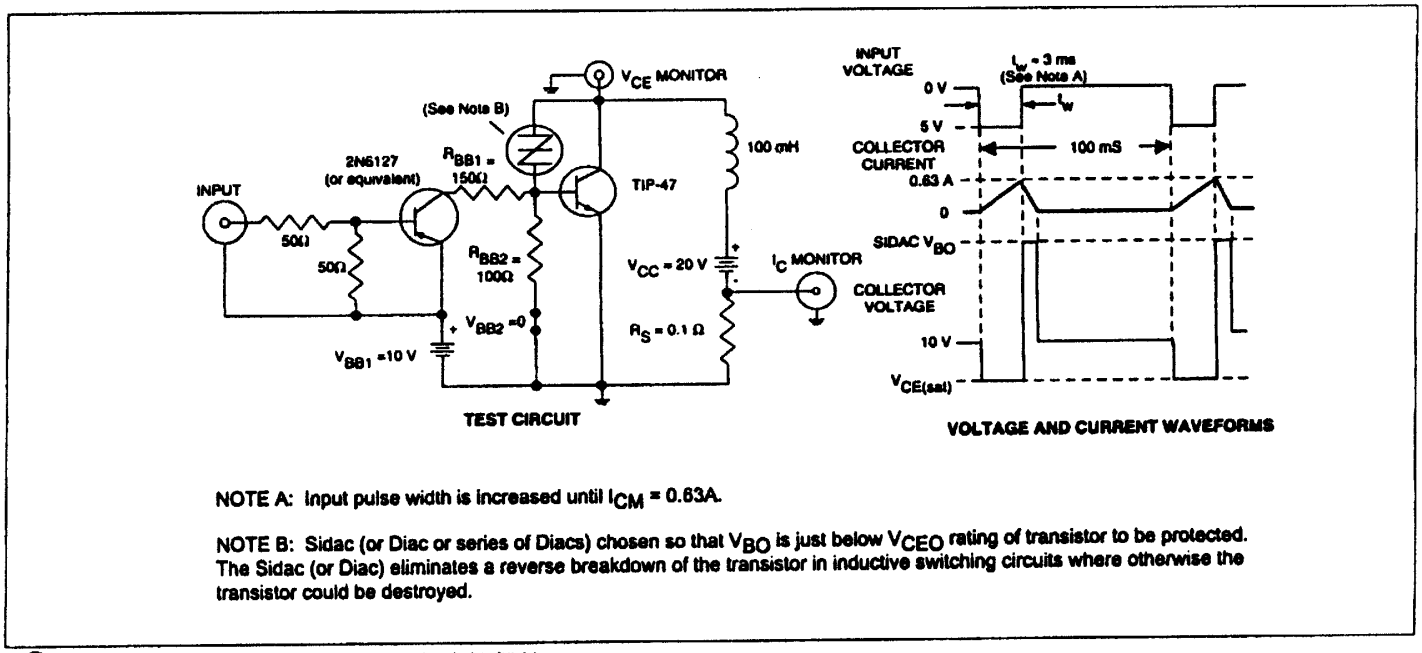
❼ 高压钠灯启动电路



❽ 典型的金属卤化物点火器电路



❾ SIDAC 弛张振荡器电路



NOTE A: Input pulse width is increased until I_{CM} = 0.63A.

NOTE B: Sidac (or Diac or series of Diacs) chosen so that V_{BO} is just below V_{CEO} rating of transistor to be protected. The Sidac (or Diac) eliminates a reverse breakdown of the transistor in inductive switching circuits where otherwise the transistor could be destroyed.

❿ SIDAC 对三极管电感负载开关电路的保护